

Technical Data
Data Sheet 3486, Rev. -

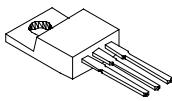
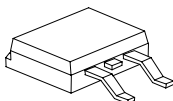
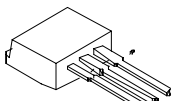
32CTQ030-G/32CTQ030S-G/32CTQ030-1-G
SCHOTTKY RECTIFIER

Applications:

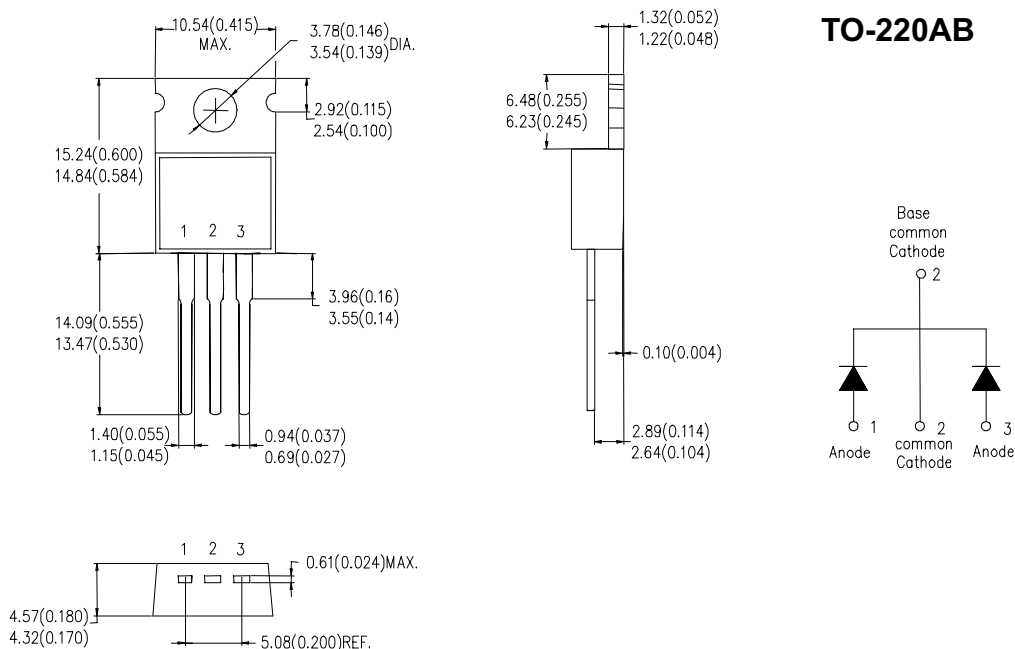
- Switching power supply • Converters • Free-Wheeling diodes • Reverse battery protection

Features:

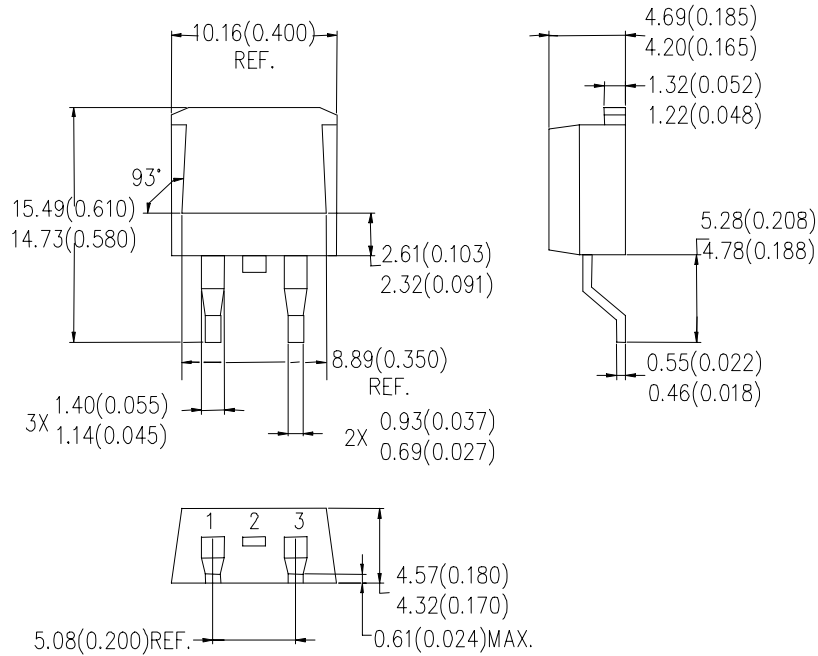
- 150°C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Green Products in Compliance with the RoHS Directive

Case styles		
32CTQ030-G  TO-220AB	32CTQ030S-G  D²PAK	32CTQ030-1-G  TO-262

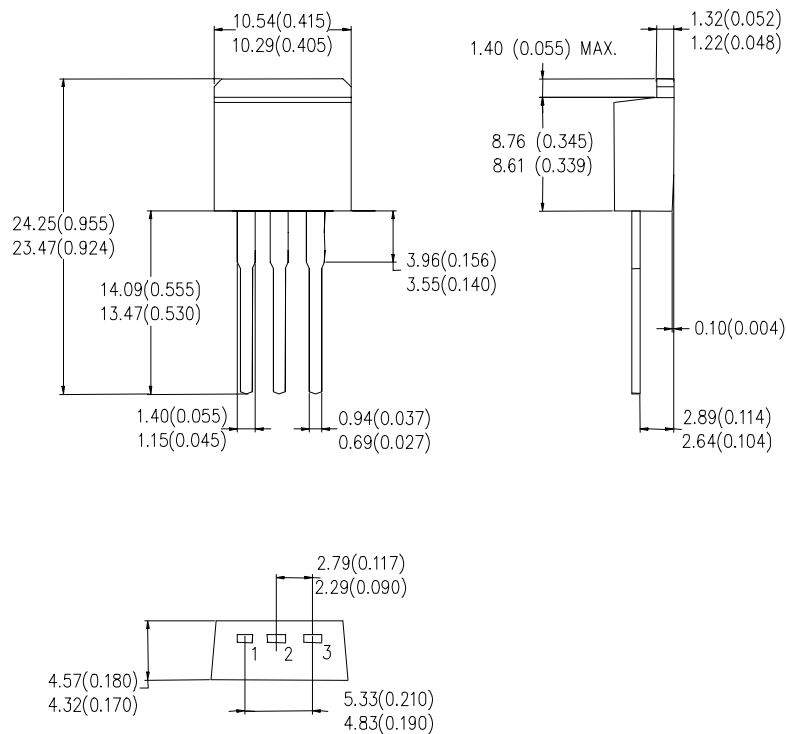
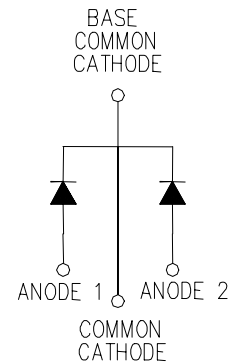
Mechanical Dimensions: In Inches / mm



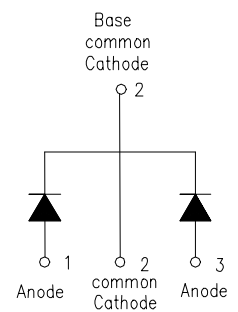
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D²PAK



TO-262



Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	30	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 115^\circ\text{C}$, rectangular wave form	30	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	300	A
Non-Repetitive Avalanche Energy	E_{AS}	$T_J = 25^\circ\text{C}$, $I_{AS} = 1.20\text{ A}$, $L = 11.10\text{ mH}$	13	mJ
Repetitive Avalanche Current	I_{AR}	Current decaying linearly to zero in 1 μsec Frequency limited by T_J max. $V_A = 1.5 \times V_R$ typical	3	A

Electrical Characteristics:

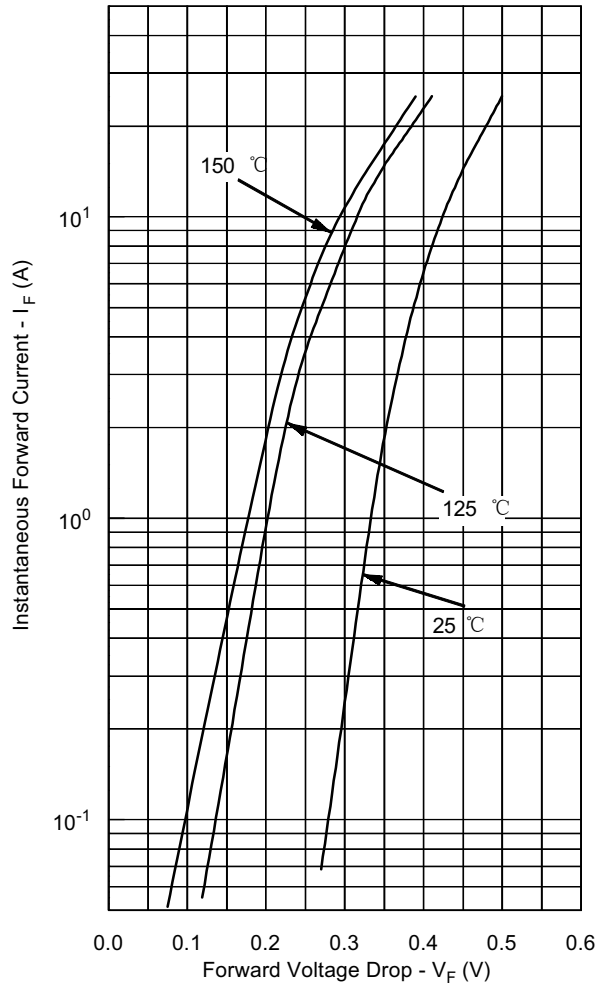
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop *	V_{F1}	@ 15 A, Pulse, $T_J = 25^\circ\text{C}$	0.49	V
		@ 30 A, Pulse, $T_J = 25^\circ\text{C}$	0.58	
	V_{F2}	@ 15 A, Pulse, $T_J = 125^\circ\text{C}$	0.40	V
		@ 30 A, Pulse, $T_J = 125^\circ\text{C}$	0.53	
Max. Reverse Current *	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	1.75	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	97	mA
Max. Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{ V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$	1300	pF
Typical Series Inductance (per leg)	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change (Rated V_R)	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

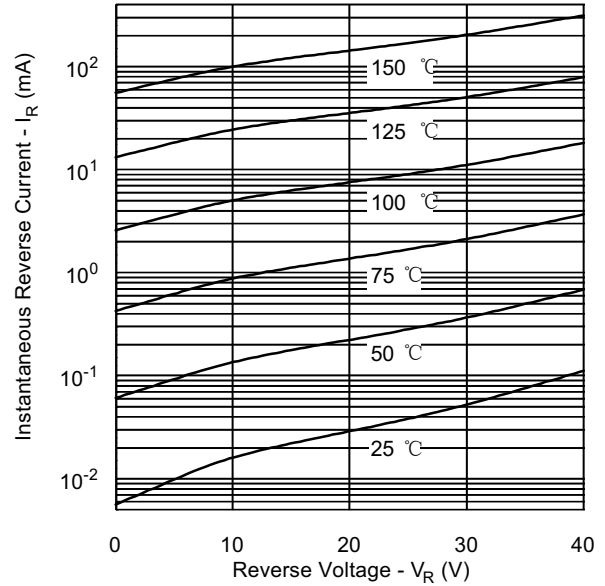
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	3.25	$^\circ\text{C/W}$
Maximum Thermal Resistance, Case to Heat Sink	$R_{\theta CS}$	Mounting surface, smooth and greased	0.50	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Mounting Torque	T_M	-	6 (min) 12 (max)	Kg-cm
Case Style	TO-220AB D ² PAK TO-262 (Suffix "s" for D ² PAK; Suffix "-1" for TO-262)			

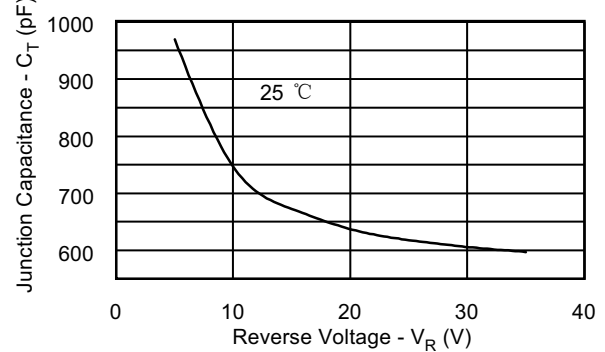
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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